# **BUK7610-100B**

# N-channel TrenchMOS standard level FET

6 July 2012

**Product data sheet** 

# 1. Product profile

## 1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

### 1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Q101 compliant
- Suitable for standard level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

# 1.3 Applications

- 12 V, 24 V and 42 V loads
- Automotive systems
- General purpose power switching
- Motors, lamps and solenoids

### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	100	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 1</u> ; <u>Fig. 3</u>	[1]	-	-	75	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	-	300	W
Static charac	cteristics						
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 11; Fig. 12		-	8.6	10	mΩ
Dynamic cha	racteristics						
$Q_{GD}$	gate-drain charge	$V_{GS}$ = 10 V; $I_D$ = 25 A; $V_{DS}$ = 80 V; $T_j$ = 25 °C; <u>Fig. 13</u>		-	22	-	nC
Avalanche ruggedness							
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$I_D$ = 75 A; $V_{sup} \le 100$ V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; unclamped		-	-	629	mJ



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[1] Continuous current is limited by package.

# **Pinning information**

Table 2. **Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D 1
2	D	drain[1]		
3	S	source	1,	G—UI—A
mb	D	mounting base; connected to drain	D2PAK (SOT404)	mbb076 S

<sup>[1]</sup> It is not possible to make connection to pin 2.

#### **Ordering information** 3.

**Ordering information** Table 3.

Type number	Package					
	Name	Description	Version			
BUK7610-100B	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404			

# **Marking**

**Marking codes** Table 4.

Type number	Marking code
BUK7610-100B	BUK7610-100B

# **Limiting values**

**Limiting values** 

BUK7610-100B

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	100	V
$V_{DGR}$	drain-gate voltage	$R_{GS}$ = 20 k $\Omega$		-	100	V
$V_{GS}$	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 10 V; <u>Fig. 1</u> ; <u>Fig. 3</u>	[1]	-	110	Α
			[2]	-	75	Α
		T <sub>mb</sub> = 100 °C; V <sub>GS</sub> = 10 V; <u>Fig. 1</u>	<u>[2]</u>	-	75	Α
I <sub>DM</sub>	peak drain current	$T_{mb}$ = 25 °C; pulsed; $t_p \le 10 \mu s$ ; Fig. 3		-	438	Α

Symbol	Parameter	Conditions		Min	Max	Unit
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	300	W
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-dra	in diode					
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	[1]	-	110	Α
			[2]	-	75	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	438	Α
Avalanche	ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$I_D$ = 75 A; $V_{sup} \le 100$ V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; unclamped		-	629	mJ

- [1] Current is limited by power dissipation chip rating.
- [2] Continuous current is limited by package.

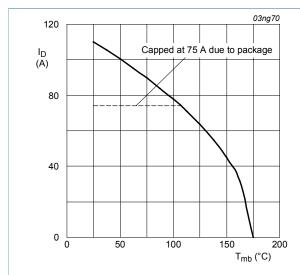


Fig. 1. Normalized continuous drain current as a function of mounting base temperature

$$V_{\rm GS} \geq 5~V$$

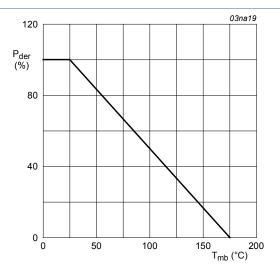


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}\text{C})}} \times 100 \,\%$$

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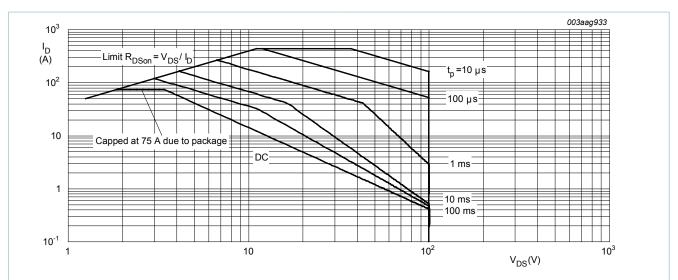


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

 $T_{mb} = 25$ °C;  $I_{DM}$  is a single pulse

# 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 4	-	-	0.5	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	mounted on printed-circuit board ; minimum footprint	-	50	-	K/W

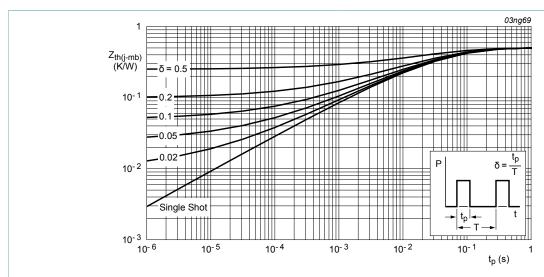


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

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# 7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics		·			
$V_{(BR)DSS}$	drain-source	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	100	-	-	V
	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 ^{\circ}\text{C}$	89	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 10	1	-	-	V
		$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C; Fig. 10	2	3	4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 10	-	-	4.4	V
I <sub>DSS</sub> drain leakage of	drain leakage current	V <sub>DS</sub> = 100 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.02	1	μΑ
		V <sub>DS</sub> = 100 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C	-	-	500	μΑ
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
		V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
Doon	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 11; Fig. 12	-	8.6	10	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; Fig. 11; Fig. 12	-	-	25	mΩ
Dynamic cl	naracteristics					
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 80 V; V <sub>GS</sub> = 10 V;	-	80	-	nC
$Q_{GS}$	gate-source charge	T <sub>j</sub> = 25 °C; <u>Fig. 13</u>	-	18	-	nC
$Q_{GD}$	gate-drain charge		-	22	-	nC
C <sub>iss</sub>	input capacitance	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 25 V; f = 1 MHz;	-	5080	6773	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 14</u>	-	677	812	pF
C <sub>rss</sub>	reverse transfer capacitance		-	168	230	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 1.2 \Omega; V_{GS} = 10 \text{ V};$	-	33	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 10 \Omega; T_j = 25 °C$	-	45	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	120	-	ns
t <sub>f</sub>	fall time		-	36	-	ns
	internal drain inductance	from drain lead 6 mm from package to centre of die ; $T_j$ = 25 °C	-	4.5	-	nH
		from upper edge of drain mounting base to centre of die ; $T_j = 25 ^{\circ}\text{C}$	-	2.5	-	nH
L <sub>S</sub>	internal source inductance	from source lead to source bond pad ; T <sub>i</sub> = 25 °C	-	7.5	-	nH

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Source-drain diode							
$V_{SD}$	source-drain voltage	$I_S = 40 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 15$		-	0.85	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$		-	69	-	ns
Q <sub>r</sub>	recovered charge	$V_{GS} = -10 \text{ V}; V_{DS} = 30 \text{ V}; T_j = 25 \text{ °C}$		-	212	-	nC

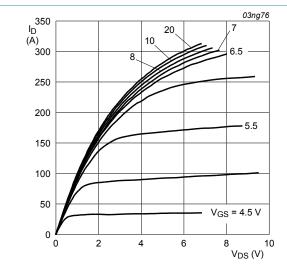


Fig. 5. Output characteristics: drain current as a function of drain-source voltage; typical values

$$T_j = 25^{\circ}C; t_p = 300\mu s$$

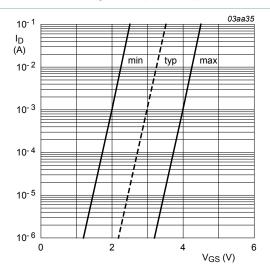


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25 \,^{\circ}C; V_{DS} = 5V$$

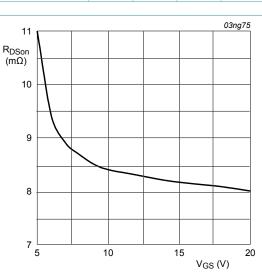


Fig. 6. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25^{\circ}C; I_D = 25A$$

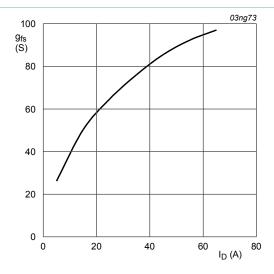


Fig. 8. Forward transconductance as a function of drain current; typical values

$$T_j = 25$$
° $C$ ;  $V_{DS} = 25V$ 

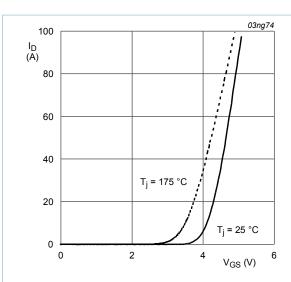


Fig. 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values



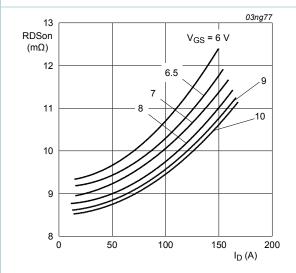


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

$$T_j=25^{\circ}C$$

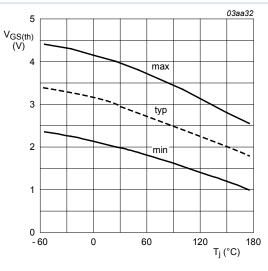


Fig. 10. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1 mA; V_{DS} = V_{GS}$$

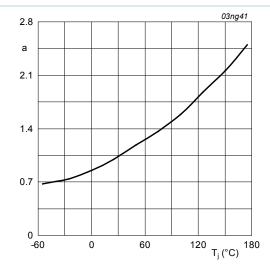


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

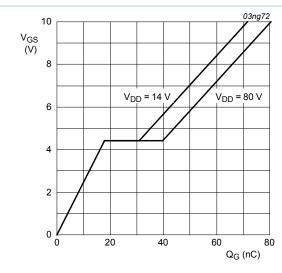


Fig. 13. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25^{\circ}C; I_D = 25A$$

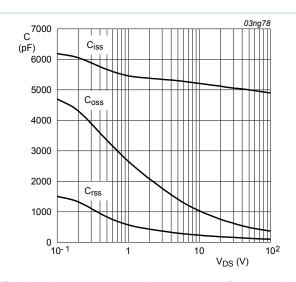


Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = 0V; f = 1MHz$$

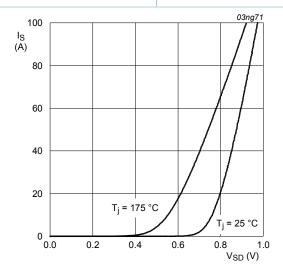


Fig. 15. Reverse diode current as a function of reverse diode voltage; typical value

$$V_{\it GS} = 0V$$

# 8. Package outline

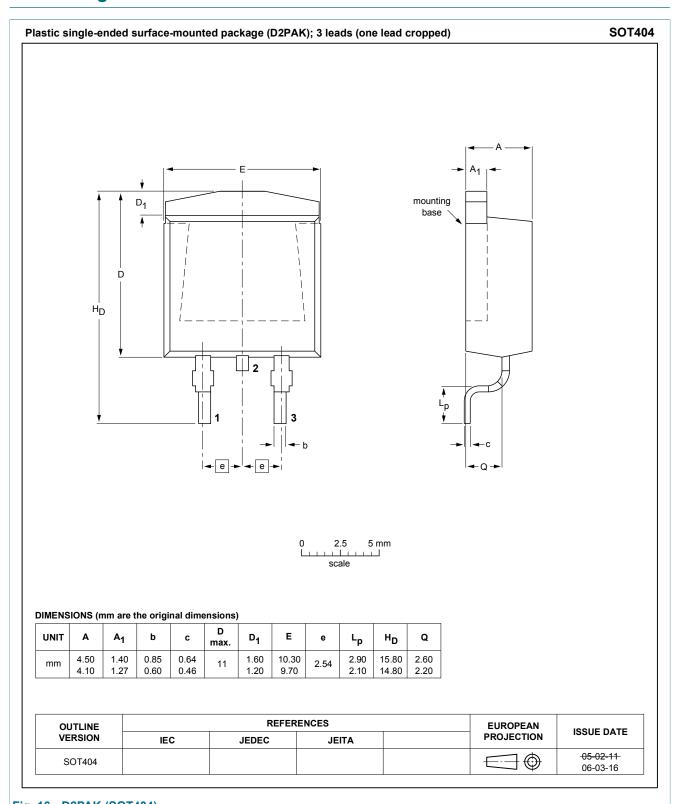


Fig. 16. D2PAK (SOT404)

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